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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/542,473	04/04/2000	Takayuki Ikeda	0756-2138	6069
22204	7590	01/22/2004	EXAMINER	
NIXON PEABODY, LLP 401 9TH STREET, NW SUITE 900 WASHINGTON, DC 20004-2128			SEFER, AHMED N	
			ART UNIT	PAPER NUMBER
			2826	

DATE MAILED: 01/22/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

09/542,473

Applicant(s)

IKEDA ET AL.

Examiner

A. Sefer

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MW

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 02 October 2003.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 3-10, 16-33 and 35-42 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☒ Claim(s) 35-42 is/are allowed.
- 6) ☒ Claim(s) 3-10 and 16-33 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. §§ 119 and 120

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
* See the attached detailed Office action for a list of the certified copies not received.
- 13) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application) since a specific reference was included in the first sentence of the specification or in an Application Data Sheet. 37 CFR 1.78.
a) ☐ The translation of the foreign language provisional application has been received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121 since a specific reference was included in the first sentence of the specification or in an Application Data Sheet. 37 CFR 1.78.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) _____
- 4) ☐ Interview Summary (PTO-413) Paper No(s). _____
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other:

DETAILED ACTION

Response to Amendment

1. The amendment filed on October 2, 2003 has been entered; no new claims have been added.

Claim Objections

2. Claim 35 is objected to because of the following informalities: The limitation "a high concentration impurity regions" should read "a high concentration impurity region".

Appropriate correction is required.

Claim Rejections - 35 USC § 112

3. The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

4. Claims 16 and 17 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

5. Claim 16 recites the limitations "said two channel forming regions" and "one of the two channel forming region". There is insufficient antecedent basis for these limitations in the claim.

6. Claim 18 recites the limitations "said two channel forming regions" and "one of the two channel forming region" and "a portion of the second impurity region". There is insufficient antecedent basis for these limitations in the claim.

Claim Rejections - 35 USC § 103

7. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

8. Claims 3-10 and 21-25 are rejected under 35 U.S.C. 103(a) as being unpatentable over Matsumoto US Patent No. 5,323,042 in view of Ikeda (JP 7-326767) and Otani (JP 10-56184).

Matsumoto discloses in fig. 1 a display device comprising a pixel portion 12 and a driver portion 13 on a substrate 11, said pixel portion comprising a semiconductor film comprising a channel forming region 21a, a plurality of impurity regions 21b, a source region 21c, and a drain region 21c; and a gate electrode 25 overlapping/partially overlapping with the channel forming region and some of the plurality of impurity regions, with a gate insulating film 24 interposed therebetween, wherein a gate insulating film of a TFT in said driver circuit portion and a dielectric of a storage capacitor formed in said pixel portion comprise the same material and have the same film thickness (as in claim 4), but omits a gate electrode overlapping plurality of channel regions/some of the plurality of impurity regions and a thicker gate film in a pixel portion than one in a driver circuit portion.

Ikeda discloses (see abstract and figs. 1-5) a display device comprising a semiconductor film having a plurality of channel regions 21 and a plurality of impurity regions 31A-C having the same conductivity type as a source 23 and drain 25 regions (as in claim 23) wherein some of the plurality of impurity regions are located between the plurality of the channel forming regions in the semiconductor film and contain a low concentration impurity region and a high concentration impurity region; and a gate electrode 14 overlapping with the plurality of channel forming regions and some of the plurality of impurity regions with a gate insulating film 13 interposed therebetween.

Otani discloses a display device comprising a thickness of a gate insulating film of a TFT in a driver circuit portion 20a; 20b is thinner than a gate insulating film of a TFT in a pixel portion 20c.

Therefore, it would have been obvious to one skilled in the art at the time the invention was made to incorporate Ikeda's teachings with Matsumoto's device since that would provide a pixel with a larger numerical aperture. It would have been obvious to incorporate the teachings of Otani, since that would execute a high-speed operation and reduce power consumption as taught by Otani.

As for claims 5 and 10, the prior art omits that electronic equipment selected from the group consisting of a video camera, a digital camera and other various electronic equipment. However, Examiner takes Official Notice that electronic equipment comprising a display device wherein said electronic equipment selected from the group consisting of a video camera or a digital camera is conventional and well known. Therefore, it would have been obvious to one skilled in the art at the time the invention was made to have used any of the various electronic equipment since Examiner takes Official Notice that due to their low power consumption, displays have become a necessary and indispensable structural element of an electronic equipment.

As to claims 6, 8 and 24, Ikeda discloses in fig. 3 a plurality of impurity regions 31 comprising a low concentration regions, a high concentration region, and wherein said some of the plurality the low concentration impurity regions and the high concentration impurity region are located between the plurality of the channel forming regions in the semiconductor film or the

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high concentration impurity region are located between a pair of low impurity regions under the gate electrode (as in claim 24).

As to claims 7, 9, 21-23 and 25, the prior art discloses at least two impurity regions overlapped with the gate electrode and at least one impurity region overlapped with the gate electrode containing an element belonging to group XV in the periodic table (as in claims 22 and 25) but does not specifically disclose having a concentration as recited in the claim. However, it would have been obvious to optimize the device by using a workable range, which involves only a routine skill in the art. Further, the specification contains no disclosure of either the critical nature of the claimed arrangement or any unexpected results arising therefrom. Where patentability is said to be based upon particular chosen dimensions or upon another variable recited in a claim, the applicant must show that the chosen dimensions are critical. In re Woodruff, 919 F.2d 1575, 1578, 16 USPQ2d 1934, 1936 (Fed. Cir. 1990).

9. Claims 4 and 23 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yeo US Patent No. 6,140,162 in view of Ikeda (JP 7-326767) and Otani (JP 10-56184).

Yeo discloses in fig. 3 a display device comprising a pixel portion and a driver portion on a substrate 200, said pixel portion comprising a semiconductor film comprising a channel forming region 41C, a plurality of impurity regions 41L, a source region 41S, and a drain region 41D; and a gate electrode 43G overlapping with the channel forming region, with a gate insulating film 42T interposed therebetween, wherein a gate insulating film 52 of a TFT in said driver circuit portion and a dielectric 42T of a storage capacitor formed in said pixel portion comprise the same material and have the same film thickness, but omits a gate electrode

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overlapping plurality of channel regions/some of the plurality of impurity regions and a thicker gate film in a pixel portion than one in a driver circuit portion.

Ikeda discloses (see abstract and figs. 1-5) a display device comprising a semiconductor film having a plurality of channel regions 21 and a plurality of impurity regions 31A-C having the same conductivity type as a source 23 and drain 25 regions (as in claim 23) wherein some of the plurality of impurity regions are located between the plurality of the channel forming regions in the semiconductor film and contain a low concentration impurity region and a high concentration impurity region; and a gate electrode 14 overlapping with the plurality of channel forming regions and some of the plurality of impurity regions with a gate insulating film 13 interposed therebetween.

Otani discloses a thickness of a gate insulating film of a TFT in a driver circuit portion 20a; 20b is thinner than a gate insulating film of a TFT in a pixel portion 20c.

Therefore, it would have been obvious to one skilled in the art at the time the invention was made to incorporate Ikeda's teachings with Matsumoto's device, since that would provide a pixel with a larger numerical aperture. It would have been obvious to incorporate the teachings of Otani, since that would execute a high speed operation and reduce power consumption as taught by Otani.

10. Claims 16, 17 and 27-29, as understood, are rejected under 35 U.S.C. 103(a) as being unpatentable over Matsumoto US Patent No. 5,323,042 in view of Ikeda (JP 7-326767) and Otani (JP 10-56184).

Matsumoto discloses in fig. 1 a display device comprising a pixel portion 12 and a driver portion 13 on a substrate 11, said pixel portion comprising a semiconductor film comprising a

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channel forming region 21a, a plurality of impurity regions 21b, a source region 21c, and a drain region 21c; and a gate electrode 25 overlapping/partially overlapping with the channel forming region and some of the plurality of impurity regions, with a gate insulating film 24 interposed therebetween, wherein a gate insulating film of a TFT in said driver circuit portion and a dielectric of a storage capacitor formed in said pixel portion comprise the same material and have the same film thickness (as in claim 29), but omits a gate electrode overlapping plurality of channel regions/some of the plurality of impurity regions and a thicker gate film in a pixel portion than one in a driver circuit portion.

Ikeda discloses (see abstract and figs. 1-5) a display device comprising a semiconductor film having at least two channel forming regions 31A and 31C, at least one first impurity region 21A, at least one second impurity region 21B, a high concentration impurity region 31B, a source region 23, and a drain region 25; wherein one of the two channel forming region is located between the first impurity region and second impurity region; and a gate electrode 14 overlapped with said two channel forming regions and the first impurity region, and a part of the second impurity region with a gate insulating film 13 interposed therebetween.

Otani discloses a display device comprising a thickness of a gate insulating film of a TFT in a driver circuit portion 20a; 20b is thinner than a gate insulating film of a TFT in a pixel portion 20c.

Therefore, it would have been obvious to one skilled in the art at the time the invention was made to incorporate Ikeda's teachings with Matsumoto's device since that would provide a pixel with a larger numerical aperture. It would have been obvious to incorporate the teachings

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of Otani, since that would execute a high-speed operation and reduce power consumption as taught by Otani.

As for claim 17, the prior art omits that electronic equipment selected from the group consisting of a video camera, a digital camera and other various electronic equipment. However, Examiner takes Official Notice that electronic equipment comprising a display device wherein said electronic equipment selected from the group consisting of a video camera or a digital camera is conventional and well known. Therefore, it would have been obvious to one skilled in the art at the time the invention was made to have used any of the various electronic equipment since Examiner takes Official Notice that due to their low power consumption, displays have become a necessary and indispensable structural element of an electronic equipment.

As to claims 27 and 28, the prior art discloses at least two impurity regions overlapped with the gate electrode and at least one impurity region overlapped with the gate electrode containing an element belonging to group XV in the periodic table (as in claim 28) but does not specifically disclose having a concentration as recited in the claim. However, it would have been obvious to optimize the device by using a workable range, which involves only a routine skill in the art. Further, the specification contains no disclosure of either the critical nature of the claimed arrangement or any unexpected results arising therefrom. Where patentability is said to be based upon particular chosen dimensions or upon another variable recited in a claim, the applicant must show that the chosen dimensions are critical. In re Woodruff, 919 F.2d 1575, 1578, 16 USPQ2d 1934, 1936 (Fed. Cir. 1990).

11. Claims 18-20 and 30-33 as understood, are rejected under 35 U.S.C. 103(a) as being unpatentable over Matsumoto US Patent No. 5,323,042 in view of Ikeda (JP 7-326767) and Otani (JP 10-56184).

Matsumoto discloses in fig. 1 a display device comprising a pixel portion 12 and a driver portion 13 on a substrate 11, said pixel portion comprising a semiconductor film comprising a channel forming region 21a, a plurality of impurity regions 21b, a source region 21c, and a drain region 21c; and a gate electrode 25 overlapping/partially overlapping with the channel forming region and some of the plurality of impurity regions, with a gate insulating film 24 interposed therebetween, wherein a gate insulating film of a TFT in said driver circuit portion and a dielectric of a storage capacitor formed in said pixel portion comprise the same material and have the same film thickness, but omits a gate electrode overlapping plurality of channel regions/some of the plurality of impurity regions and a thicker gate film in a pixel portion than one in a driver circuit portion.

Ikeda discloses (see abstract and figs. 1-5) a display device comprising a semiconductor film having at least two channel forming regions 21, first low concentration impurity regions 31A, a second low concentration impurity region 31C, a high concentration impurity region 31B, a source region 23, and a drain region 25; wherein the high concentration impurity region is located between the two channel forming regions or between a pair of low concentration impurity regions (as in claim 31); and a gate electrode 14 overlapping with said two channel forming regions, the first low concentration impurity regions, the high concentration impurity region, and a portion of the second impurity region, with a gate insulating film 13 interposed therebetween.

Otani discloses a display device comprising a thickness of a gate insulating film of a TFT in a driver circuit portion 20a; 20b is thinner than a gate insulating film of a TFT in a pixel portion 20c (as in claim 19).

Therefore, it would have been obvious to one skilled in the art at the time the invention was made to incorporate Ikeda's teachings with Matsumoto's device since that would provide a pixel with a larger numerical aperture. It would have been obvious to incorporate the teachings of Otani, since that would execute a high-speed operation and reduce power consumption as taught by Otani.

As for claim 20, the prior art omits that electronic equipment selected from the group consisting of a video camera, a digital camera and other various electronic equipment. However, Examiner takes Official Notice that electronic equipment comprising a display device wherein said electronic equipment selected from the group consisting of a video camera or a digital camera is conventional and well known. Therefore, it would have been obvious to one skilled in the art at the time the invention was made to have used any of the various electronic equipment since Examiner takes Official Notice that due to their low power consumption, displays have become a necessary and indispensable structural element of an electronic equipment.

As for claim 30, Ikeda discloses the first low concentration impurity regions 31A, the second low concentration impurity region 31C, and the high concentration impurity region 31B having the same conductivity type as the source 23 and drain 25 regions.

As to claims 32 and 33, the prior art discloses at least two impurity regions overlapped with the gate electrode and at least one impurity region overlapped with the gate electrode containing an element belonging to group XV in the periodic table (as in claim 33) but does not

specifically disclose having a concentration as recited in the claim. However, it would have been obvious to optimize the device by using a workable range, which involves only a routine skill in the art. Further, the specification contains no disclosure of either the critical nature of the claimed arrangement or any unexpected results arising therefrom. Where patentability is said to be based upon particular chosen dimensions or upon another variable recited in a claim, the applicant must show that the chosen dimensions are critical. In re Woodruff, 919 F.2d 1575, 1578, 16 USPQ2d 1934, 1936 (Fed. Cir. 1990).

Allowable Subject Matter

12. Claims 35-42 are allowed.
13. The following is a statement of reasons for the indication of allowable subject matter:
The prior art fails to disclose a device structure as recited in claim 35.
14. Claim 26 would be allowable if rewritten to overcome the rejection(s) under 35 U.S.C. 112, second paragraph, set forth in this Office action and to include all of the limitations of the base claim and any intervening claims.

Conclusion

15. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Yamazaki et al. US ref. 6,278,131 disclose a pixel TFT having a driver circuit portion with thinner gate oxide than the one of a pixel portion.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to A. Sefer whose telephone number is (703) 605-1227.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (703) 308-6601.

ANS

January 6, 2004

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WASHINGTON, D.C. 20535

